

c. **Amendments to Claims**

1 – 7. (Cancelled)

8. (Currently amended) A process for making a structure, comprising:
5 providing a solid body of comprising MgB₂;
ejecting MgB₂ from the body by directing laser light onto the body; and
growing an MgB₂ layer on a surface of a substrate with ~~from~~ a portion of the
ejected MgB₂.

10 9. (Original) The process of claim 8, wherein the substrate and MgB₂
have lattice constants along the surface that match to at least 10 percent.

10. (Original) The process of claim 8, further comprising forming the solid body
by sintering MgB₂.

15 11. (Original) The process of claim 8, wherein the ejecting includes directing
light from a pulsed laser onto the body.

12. (Currently Amended) The process of claim 8, wherein the substrate
20 comprises one of SiC, LaAlO₃, ~~SiO₂~~, SrTiO₃, and sapphire.

13. (Original) The process of claim 8, wherein the ejecting and growing are
performed in a vacuum chamber that is maintained at a pressure of less than about 10⁻²
Torr.

25 14. (Currently amended) The process of claim 14 ~~8~~, wherein the ejecting and
growing are performed in a vacuum chamber that is maintained at a pressure of greater
than about 10⁻⁶ Torr.

30 15. (Original) The process of claim 13, wherein the growing produces a
crystalline or polycrystalline layer of MgB₂ whose thickness is at least 10 nm.

16. (New) The process of claim 8, wherein the solid body is a solid body of MgB₂.

17. (New) The process of claim 8, wherein the MgB₂ layer is grown from a
5 portion of the ejected MgB₂.

18. (New) The process of claim 17, wherein the solid body is a solid body of MgB₂.